

Type	Hits	Search Text	DBs	Time Stamp
Per	1	BRS 0 (gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	USPAT	2001/03/19
Acti	2	BRS 1 (gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	USPAT	2001/03/19
Fail	3	BRS 0 (gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	EPO; JPO; DERWENT; IBM	2001/03/19
Sav	4	BRS 11 ((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))	EPO; JPO; DERWENT; IBM	2001/03/20
	5	BRS 28 (((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))) and ((semic	USPAT	2001/03/20
	6	(((gate adj insulator) or dielectric) with ((silicon adj oxide) and (nitride or nitrogen) and (fluori\$))) and ((semic	USPAT	2001/03/20
	7	BRS 16 halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))	USPAT	2001/03/20
	8	BRS 1 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20
	9	BRS 1 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20
	10	BRS 13 (semiconductor adj device) and ((nitrogen adj concentration) with oxynitride)	USPAT	2001/03/20
	11	BRS 1 (halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/03/20
	12	BRS 11 ((halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectr	USPAT	2001/03/20
	13	BRS 1 5869858.bn.	USPAT	2001/03/20
	14	BRS 1 5866930.bn.	USPAT	2001/03/20
	15	BRS 1 5831319.bn.	USPAT	2001/03/20
	16	BRS 1 5814863.bn.	USPAT	2001/03/20
	17	BRS 1 5753564.bn.	USPAT	2001/03/20
	18	BRS 0 ((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and ((insulating or dielectric) adj film)).ab	USPAT	2001/03/20
	19	BRS 0 ((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and (insulating or dielectric)).ab.	USPAT	2001/03/20
	20	BRS 0 ((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and (insulating or dielectric)).clm.	USPAT	2001/03/20
	21	BRS 0 (((halogen or fluor\$) and (nitrogen or nitride).and (silicon) and (oxy\$) and (insulating or dielectric))) and (sem	USPAT	2001/03/20
	22	BRS 0 (((halogen or fluor\$) and (nitrogen or nitride) and (silicon) and (oxy\$) and (insulating or dielectric))) and (sem	USPAT	2001/03/20
	23	BRS 8 (halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectric))	EPO; JPO; DERWENT; IBM	2001/03/20
	24	BRS 0 (nitrogen adj concentration) with ((insulating or dielectric) adj film)	US-PGPUB	2001/03/20
	25	BRS 2 (semiconductor adj device).ti.	US-PGPUB	2001/03/20
	26	BRS 4 ((nitrogen adj concentration) with ((insulating or dielectric) adj film)) and (halogen or fluor\$)	USPAT	2001/03/20
	27	BRS 15 (atomic adj percent) same (atomic adj concentration)	USPAT	2001/03/21
	28	BRS 1 6191463.bn.	USPAT	2001/03/21
	29	BRS 25 ((gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)) and (nitrogen with conce	USPAT	2001/09/20
	30	BRS 1 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/09/21
	31	BRS 2 (halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	EPO; JPO; DERWENT; IBM	2001/09/21
	32	BRS 34 (halogen with (insulat\$ or dielectric)) and (semiconductor adj device) and (nitrogen with (insulat\$ or dielectric))	USPAT	2001/09/21
	33	BRS 2 ((halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	USPAT	2001/09/21
	34	BRS 2 (halogen same (insulating with ((layer or film) and (silicon) and (oxygen) and (nitrogen)))) and (semiconductor	EPO; JPO; DERWENT; IBM	2001/09/22
	35	BRS 36 (gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)	USPAT	2001/09/22
	36	BRS 36 (gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping)	USPAT	2001/09/22
	37	BRS 5 ((gate adj (insulator or dielectric or insulating)) with (halide or halogen or fluorine or bromine or chlorine or iod	USPAT	2001/09/23
	38	BRS 36 ((gate adj (insulator or dielectric or insulating)) with nitrogen with (doped or doping))	USPAT	2001/09/23
	39	BRS 0 ((spacer) with (source or drain)) and ("JP 11111845 A".DID. and (((gate adj insulator) or dielectric) with ((sil	USPAT	2001/09/23

Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Detail	Errors
File	1						

Type	Hk#	Search Text	DBs	Time Stamp
Draw	40	((spacer) with (source or drain) and (((source or drain) with (beside) with (gate)))	USPAT	2001/09/23
Per	41	((spacer with (source or drain) with polysilicon) not ((ldd or (lightly adj doped).ab.)) and ("spacer is drain")	USPAT	2001/09/23
Act	42	((spacer with (source or drain) with polysilicon) not ((ldd or (lightly adj doped).ab.)) and ("spacer is" adj (drai	USPAT	2001/09/23
Fail	43	((lateral with transistor) and (spacer with polysilicon) not ((bipolar or bjt).ab.)) and ((source or drain) with ab	USPAT	2001/09/23
Can	44	((lateral with transistor) and (spacer with polysilicon) not ((bipolar or bjt).ab.)) and ((source or drain) with ab	USPAT	2001/09/23
Can	45	((lateral with transistor) and (spacer with (polysilicon or silicon))) not ((bipolar or bjt).ab.)) and ((source or dr	USPAT	2001/09/23
Can	46	((lateral with transistor) and (spacer with (polysilicon or silicon))) not ((bipolar or bjt).ab.)) and ((source or dr	USPAT	2001/09/23
Can	47	(polysilicon adj (drain or source) adj spacer)	USPAT	2001/09/23
Can	48	(silicon adj (drain or source) adj spacer)	USPAT	2001/09/23
Can	49	((silicon adj (drain or source)) with spacer)	USPAT	2001/09/23
Can	50	((raised or elevated adj (source or drain)) not ((soi or (silicon adj on adj insulator).ab)) and ((polysilicon or s	USPAT	2001/09/23
Can	51	(morosawa and narihiro).in.	DERWENT	2001/09/23
Can	52	(morosawa).in.	DERWENT	2001/09/23
Can	53	3923559.pn.	USPAT	2001/09/23
Can	54	((nitrogen with concentration) with ("cm.sub.") with (gate adj (insulation or insulator or dielectric)))	USPAT	2001/09/23
Can	55	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric)))	USPAT	2001/09/23
Can	56	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) same ("cm.sub.")	USPAT	2001/09/23
Can	57	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) same ("cm.sup.")	USPAT	2001/09/23
Can	58	((nitrogen with concentration) with (gate adj (insulation or insulator or dielectric))) and (nitrogen with ("cm.sup	USPAT	2001/09/23
Can	59	6191463.pn. and (concentration)	USPAT	2001/09/23
Can	60	6191463.pn. and (nitrogen)	USPAT	2001/09/23
Can	61	4016587.pn.	USPAT	2001/09/23
Can	62	"4016587"	USPAT	2002/01/14
Can	63	(diffusion adj width) and (gate adj width)	USPAT	2002/01/14
Can	64	(diffusion adj width) with different	USPAT	2002/01/14
Can	65	(diffusion adj width) with (minimize)	USPAT	2002/01/14
Can	66	(diffusion adj width) with (minimal)	USPAT	2002/01/14
Can	67	(diffusion adj width) with (reduce)	USPAT	2002/01/14
Can	68	array and ((diffusion adj width) with (area))	USPAT	2002/01/14
Can	69	(diffusion adj width) with (area)	USPAT	2002/01/14
Can	70	(diffusion adj width) with (area)	USPAT	2002/01/14
Can	71	(channel adj width) with (area) with (fox or (field adj (oxide or oxidation))) with (reduce or decrease or minimiz	US-PGPUB; EPO; JPO; DE	2002/01/14
Can	72	(channel adj width) with (area) with (fox or (field adj (oxide or oxidation))) with (reduce or decrease or minimiz	US-PGPUB; EPO; JPO; DE	2002/01/14
Can	73	(dense or denser) and ((channel adj width) with (area) with (reduce or decrease or minimize))	USPAT	2002/01/14
Can	74	"5053840".PN.	USPAT	2002/01/14
Can	75	BRS 1 "4377818".PN.	USPAT	2002/01/14
Can	76	BRS 1 "4630085".PN.	USPAT	2002/01/14
Can	77	BRS 1 "4763177".PN.	USPAT	2002/01/14
Can	78	BRS 20 (integration) and ((channel adj width) with (area) with (reduce or decrease or minimize))	USPAT	2002/01/14

Type	Hk#	Search Text	DBs	Time Stamp	Comments	Error Defined	Errors
Draw	40	((spacer) with (source or drain) and (((source or drain) with (beside) with (gate)))	USPAT	2001/09/23			

Type	Hits	Search Text	DBs	Time Stamp
Per	79	BRS 0 (cmos with (gate adj array)) and (denser) and (channel adj width)	USPAT	2002/01/14
Act	80	BRS 10 (cmos with (gate adj array)) and ((area) with (channel adj width))	USPAT	2002/01/14
Fail	81	"5285069"	USPAT	2002/01/14
Save	82	BRS 4 "5629548"	USPAT	2002/01/14
	83	BRS 5 adjustable adj gate adj width	USPAT	2002/01/14
	84	BRS 0 (master adj slice) and (width with (change or changed or adjust or adjusted or reduce or reduced or decrease	USPAT	2002/01/14
	85	(master adj slice) and (width with (change or changed or adjust or adjusted or reduce or reduced or decrease	USPAT	2002/01/14
	86	BRS 12 (master adj slice) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduce	US-PGPUB; EPO; JPO; DE	2002/01/14
	87	BRS 10 (master adj slice) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduce	USPAT	2002/01/14
	88	BRS 3 (gate adj array) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduced	USPAT	2002/01/14
	89	BRS 1 (gate adj array) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduced	US-PGPUB; EPO; JPO; DE	2002/01/14
	90	BRS 2 ((gate adj array) and ((channel adj width) with (change or changed or adjust or adjusted or reduce or reduced	USPAT	2002/03/02
	91	BRS 15 (narihiro and morosawa).in.	JPO	2002/03/02
	92	BRS 6 "5821172"	USPAT	2002/03/02
	93	BRS 5 "5821172" and nitrogen	USPAT	2002/03/02
	94	BRS 3 "5821172" and (nitrogen with concentration)	USPAT	2002/03/02
	95	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with halogen with ("F" or fluorine or fluori	USPAT	2002/03/07
	96	BRS 5 (morosawa and iwata).in.	JPO; DERVENT	2002/03/07
	97	BRS 7 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	98	BRS 24 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and con	USPAT	2002/03/07
	99	BRS 35 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride))	USPAT	2002/03/07
	100	BRS 7 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and am	USPAT	2002/03/07
	101	BRS 23 ((n or nitrogen) with { atomic or at) with ("% or percent or percentage)) and (((silicon adj (oxide or dioxide)) o	USPAT	2002/03/07
	102	BRS 1 6191463.pn.	USPAT	2002/03/07
	103	BRS 0 6191463.pn. and (nitrogen with boron)	USPAT	2002/03/07
	104	BRS 1 6191463.pn. and (nitrogen same boron)	USPAT	2002/03/07
	105	BRS 1 6191463.pn. and (nitrogen)	USPAT	2002/03/07
	106	BRS 1 6191463.pn. and (nm)	USPAT	2002/03/07
	107	BRS 6 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	108	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	109	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	110	BRS 1 "6191463"	USPAT	2002/03/07
	111	BRS 30 ((doping adj concentration) with approximately) and (substrate.clm.) and "2001"	USPAT	2002/03/07
	112	BRS 7 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	113	BRS 1 "4755865".PN.	USPAT	2002/03/07
	114	BRS 1 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/07
	115	BRS 12 ("4755865"	USPAT	2002/03/07
	116	BRS 14 ("4755865"	USPAT	2002/03/07
	117	BRS 1 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F" or fluorine or fluoride)) and (con	USPAT	2002/03/08

Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Detail	Errors

Type	Hits	Search Text	DBs	Time Stamp
Per	118	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT		2002/03/08
Act	119	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT		2002/03/08
Fail	120	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT		2002/03/08
Save	121	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and ((nit)USPAT		2002/03/08
Print	122	BRS 0 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT		2002/03/10
Print	123	BRS 15 ((gate adj (insulator or insulating or dielectric or oxide)) with nitrogen with ("F or fluorine or fluoride) and (contUSPAT		2002/03/10
Print	124	BRS 0 10-365861.did.	JPO; DERWENT	2002/03/10
Print	125	BRS 0 10365861.did.	JPO; DERWENT	2002/03/10
Print	126	BRS 5 (narihiro and morosawa and iwata).in.	JPO	2002/03/10
Print	127	BRS 5 (narihiro and morosawa and iwata).in.	JPO	2002/03/10
Print	128	BRS 5 (narihiro and morosawa and iwata).in.	JPO; DERWENT	2002/03/10
Print	129	BRS 5 (morosawa and iwata).in.	JPO; DERWENT	2002/03/10
Print	130	BRS 11 (iwata).in. and (sharp.as.) and nitrogen	JPO; DERWENT	2002/03/10
Print	131	BRS 3 (morosawa).in. and (sharp.as.) and nitrogen	JPO; DERWENT	2002/03/10
Print	132	BRS 0 (maximum adj concentration) with nitrogen with (gate adj (oxide or dielectric or insulator or insulating or insulation))	USPAT	2002/03/10
Print	133	BRS 5 (maximum adj concentration) with (gate adj (oxide or dielectric or insulator or insulating or insulation))	USPAT	2002/03/10
Print	134	BRS 1 "4085498".PN.	USPAT	2002/03/10
Print	135	BRS 1 (" 4085498"	USPAT	2002/03/10
Print	136	BRS 4 ("4085498"	USPAT	2002/03/10
Print	137	BRS 1 "6013553".PN.	USPAT	2002/03/10
Print	138	BRS 1 "6140024".PN.	USPAT	2002/03/10
Print	139	BRS 1 "5567638".PN.	USPAT	2002/03/10
Print	140	BRS 18 (high adj concentration) with nitrogen with (gate adj (oxide or dielectric or insulator or insulating or insulation))	USPAT	2002/03/10
Print	141	BRS 31 "5567638"	USPAT	2002/03/10
Print	142	BRS 12 "5567638" and (nitrogen with concentration)	USPAT	2002/03/10
Print	143	BRS 5 "5674788" and ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concent	USPAT	2002/03/10
Print	144	BRS 1 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and (USPAT	2002/03/10
Print	145	BRS 35 nitrogen with "1.times.10.sup.21"	USPAT	2002/03/10
Print	146	BRS 8 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and (USPAT	2002/03/10
Print	147	BRS 37 nitrogen with "1.times.10.sup.20"	USPAT	2002/03/10
Print	148	BRS 0 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and (USPAT	2002/03/10
Print	149	BRS 6 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj concentration))) and (USPAT	2002/03/10
Print	150	BRS 14 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrogen adj implant)))	USPAT	2002/03/10
Print	151	BRS 4 nitrogen with "1.times.10.sup.22"	USPAT	2002/03/10
Print	152	BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo	USPAT	2002/03/10
Print	153	BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo	USPAT	2002/03/10
Print	154	BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo	USPAT	2002/03/10
Print	155	BRS 0 (((gate adj (insulator or insulating or dielectric or oxide or insulation)) with nitrogen with ("F or fluorine or fluo	USPAT	2002/03/10
Print	156	BRS 15 "5571734"	USPAT	2002/03/10

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④ Per 157 BRS 12 "5571734" and concentration USPAT 2002/03/10

④ Acti 158 BRS 8 "5571734" and (concentration with (nitrogen or fluorine)) USPAT 2002/03/10

④ Fail 159 BRS 4 ("4016587" USPAT 2002/03/11

④ Sav 160 BRS 1 (6191463.pn.) and boron USPAT 2002/03/11

④ (161 BRS 1 (6191463.pn.) and nitrogen USPAT 2002/03/11

④ (162 BRS 2 "5674788" and fluorine USPAT 2002/03/11

④ (163 BRS 2 "5674788" and fluorine and nitrogen USPAT 2002/03/11

④ (164 BRS 1 5674788.pn. and thickness USPAT 2002/03/11

④ (165 BRS 5 "5674788" and nm USPAT 2002/03/11

④ (166 BRS 1 5397720.pn. USPAT 2002/03/11

④ (167 BRS 20 "5397720" and (angstrom or nm) USPAT 2002/03/11

④ (168 BRS 11 ((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitridation) and ((gate adj (oxide or in USPAT 2002/09/11

④ (169 BRS 8 ((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitrided) and ((gate adj (oxide or ins USPAT, US-PGPUB 2002/09/11

④ (170 BRS 27 ((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitride)and (fluorine with (channel or USPAT, US-PGPUB 2002/09/11

④ (171 BRS 1 "5940699" PN. USPAT 2002/09/11

④ (172 BRS 22 (fluorine with gate with order) USPAT, US-PGPUB 2002/09/12

④ (173 BRS 27 (fluorine with gate) and (fluorine with (injected or injection)) USPAT, US-PGPUB 2002/09/12

④ (174 BRS 8 ((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitride)and (fluorine with (channel or USPAT, US-PGPUB 2003/05/07

④ (175 BRS 6 (MOROSAWA and NARIHIRO and IWATA and HIROSHI).in. EPO, JPO, DERVENT, IBM 2003/05/07

④ (176 BRS 6 (MOROSAWA and NARIHIRO and IWATA and HIROSHI).in. EPO, JPO, DERVENT, IBM 2003/05/07

④ (177 BRS 15 ((gate adj (oxide or insulator or insulating or insulation or dielectric) with nitridation) and ((gate adj (oxide or in USPAT, US-PGPUB 2003/05/07

④ (178 BRS 10 gate with nitrogen with boron with fluorine USPAT 2003/05/19

④ (179 BRS 2 gate with nitrogen with boron with fluorine EPO, JPO, DERVENT 2003/05/19

④ (180 BRS 0 ((fet or transistor).ab.) and ((gate adj insulator) with ((silicon adj oxide) and (nitride or nitrogen) and (flouri\$))) USPAT 2003/05/19

④ (181 BRS 0 transconductance with boron with diffusion USPAT 2003/05/19

④ (182 BRS 2 ((flat adj band) with fluorine) same ((flat adj band) with gate) USPAT 2003/09/04

④ (183 BRS 0 ((flat adj band) with fluorine) same ((flat adj band) with gate) EPO, JPO, DERVENT, IBM 2003/09/04

④ (184 BRS 0 ((flat adj band) with fluorine) same ((flat adj band) with gate) EPO, JPO, DERVENT, IBM 2003/09/04

④ (185 BRS 2 ((flat adj band) with fluorine) same ((flat adj band) with gate) USPAT 2003/09/04

④ (186 BRS 1 ((flat adj band) with fluorine) same ((flat adj band) with gate) US-PGPUB 2003/09/04

④ (187 BRS 2 (flat adj band) with fluorine with gate USPAT 2003/09/04

④ (188 BRS 2 (flat adj band) with fluorine with gate USPAT 2003/09/04

④ (189 BRS 1 (flat adj band) with fluorine with gate US-PGPUB 2003/09/04

④ (190 BRS 3 transconductance with fluorine with gate USPAT 2003/09/04

④ (191 BRS 3 transconductance with fluorine with gate USPAT 2003/09/04

④ (192 BRS 0 transconductance with fluorine with gate US-PGPUB 2003/09/04

④ (193 BRS 1 transconductance with boron with gate USPAT 2003/09/04

④ (194 BRS 0 (flat\$1band) with fluorine with gate USPAT 2003/09/04

④ (195 BRS 0 (flat\$1band) with fluorine with gate USPAT 2003/09/04

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Type	Text	Search Text	DBs	Time Stamp
Per	188 BRS 2 (flat adj band) with fluorine with gate		USPAT	2003/09/04
Act	189 BRS 1 (flat adj band) with fluorine with gate		US-PGPUB	2003/09/04
Fail	190 BRS 3 transconductance with fluorine with gate		USPAT	2003/09/04
Sav	191 BRS 3 transconductance with fluorine with gate		USPAT	2003/09/04
(192 BRS 0 transconductance with fluorine with gate		US-PGPUB	2003/09/04
(193 BRS 1 transconductance with boron with gate		USPAT	2003/08/04
(194 BRS 0 (flat\$1band) with fluorine with gate		USPAT	2003/09/04
(195 BRS 0 (flat\$1band) with fluorine with gate		USPAT	2003/09/04
(196 BRS 0 (flat\$1band) with fluorine with gate		US-PGPUB	2003/09/04
(197 BRS 1 transconductance with boron with gate		USPAT	2003/08/04
(198 BRS 4 transconductance with boron with gate		US-PGPUB	2003/09/04
(199 BRS 7 transconductance with threshold with diffusion		USPAT	2003/09/04
(200 BRS 0 (transconductance with boron with gate) and (@ad<19991224 or @rlad<19991224)		US-PGPUB	2003/09/04
(201 BRS 8 transconductance with threshold with diffusion		USPAT	2003/09/04
(202 BRS 8 (transconductance with threshold with diffusion) and (@ad<19991224 or @rlad<19991224)		USPAT	2003/09/04
(203 BRS 16 transconductance with diffusion with gate		USPAT	2003/09/04
(204 BRS 16 transconductance with diffusion with gate		USPAT	2003/09/04
(205 BRS 1 transconductance with diffusion with gate		US-PGPUB	2003/09/04
(206 BRS 21 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(207 BRS 0 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/08/04	
(208 BRS 23 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(209 BRS 15 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrided or nitridation))and (fluorine	USPAT; US-PGPUB	2003/09/04	
(210 BRS 16 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with (nitrided or nitridation)) and (fluorine	USPAT; US-PGPUB	2003/09/04	
(211 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(212 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(213 BRS 4 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(214 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(215 BRS 8 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride)and (fluorine with (channel or	USPAT; US-PGPUB	2003/09/04	
(216 BRS 0 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(217 BRS 6 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(218 BRS 0 (((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitridation) and ((gate adj (oxide or in	USPAT; US-PGPUB	2003/09/04	
(219 BRS 9 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride)and (fluorine with (channel or	USPAT; US-PGPUB	2003/09/04	
(220 BRS 8 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride)and (fluorine with gate with o	USPAT; US-PGPUB	2003/09/04	
(221 BRS 10 ((gate adj (oxide or insulator or insulating or insulation or dielectric)) with nitride)and (fluorine with gate with o	USPAT; US-PGPUB	2003/09/04	
(222 BRS 5 "6191463"		USPAT; US-PGPUB	2003/09/04
(223 BRS 3 "5674788" and (fluorine)		USPAT	2003/09/04
(224 BRS 3 "5674788" and (fluorine)		USPAT	2003/09/04
(225 BRS 0 "5674788" and (fluorine)		US-PGPUB	2003/09/04
(226 BRS 7 "6191463"		USPAT; US-PGPUB	2003/09/04

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